

GREAT AMERICAN ELECTROINCS

2N5178

Silicon NPN high power UHF transistor 2N5178 is designed for power amplifier, frequency multiplier or auto-oscillator applications in industrial equipment (class C).

Output Power:	40 Watt (typ)
Frequency Range:	100-500 Mhz
Voltage:	28 V
Package Type:	FO-85
Common Emitter Configuration	
Ballast Emitter Resistors	
Aluminum Metalization	

Electrical Characteristics (T_{CASE}=40°C)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Pout	f _o = 500 Mhz/V _{cc} =28V/P _{IN} =20W	35	40	50	W
G	f _o = 500 Mhz/V _{cc} =28V/P _{out} =40W	3			dB
λ_{c}	$f_{o} = 500 \text{ Mhz /V}_{cc} = 28 \text{V/P}_{out} = 20 \text{W}$	45	55		%

ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

SYMBOL	PARAMETERS	VALUE	UNIT
V _{CER}	Collector-Emitter Voltage $R_{EB} \le 10 \Omega$	60	V
V _{EBO}	Emitter-Base Voltage	3.5	V
I _c	Continuous Collector Current	2	A
Pc	Collector Power Dissipation	54*	W
T _i	Junction Temperature	160	°C
R _{th} (j-c)	Junction-Case Thermal Resistance	2.5	°C/W

*For Dynamic Operation, T_{CASE} = 40°C